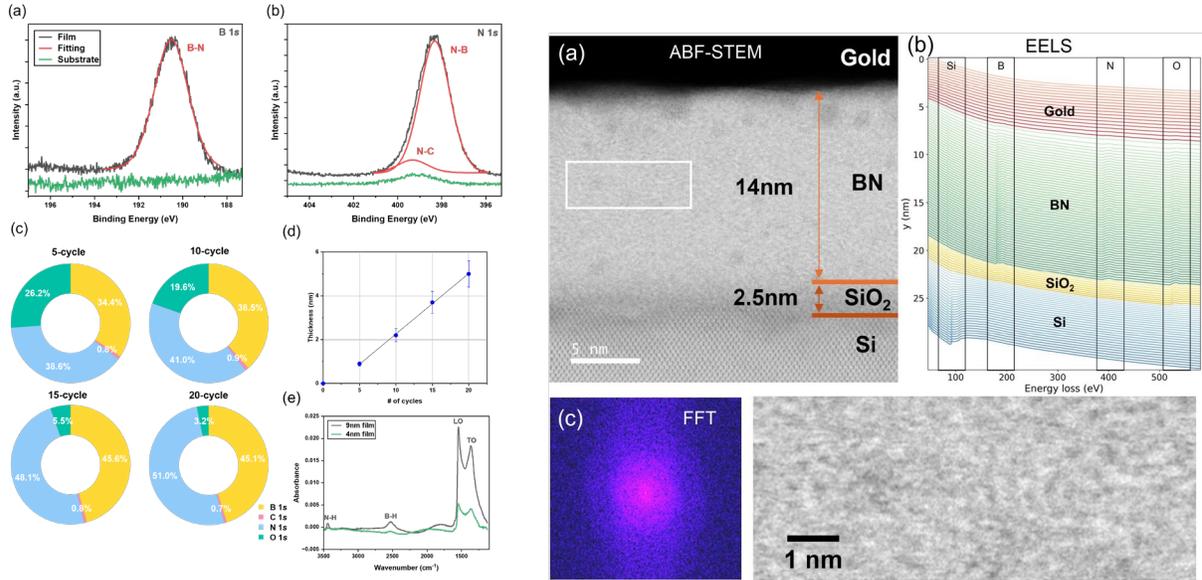


Plasma-Enhanced Growth of Low- κ Amorphous Boron Nitride: From 25 °C to 400 °C

(Left) Growth characteristics and bonding structure of a-BN films deposited by room-temperature PE-growth.

(Right) Structural and spectroscopic characterization of a MIM capacitors (Au/a-BN/SiO₂/Si).



Structural Transition from 25 °C to 400 °C: Short-range Ordered Lamellae (Top: TEM; Bottom: FFT)

